

<b>Notice of References Cited</b>	Application/Control No. 10/692,029	Applicant(s)/Patent Under Reexamination SHAO ET AL.	
	Examiner Livius R. Cazan	Art Unit 3729	Page 1 of 2

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6624040			
*	B	US-6271084			
*	C	US-5936831			
*	D	US-5920790			
*	E	US-6472721			
*	F	US-6949442			
*	G	US-6472124			
*	H	US-6825080			
*	I	US-6426249			
*	J	US-6551919			
*	K	US-6384442			
*	L	US-6479850			
*	M	US-6717193			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
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**NON-PATENT DOCUMENTS**

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	10/692,029	SHAO ET AL.	
	Examiner	Art Unit	Page 2 of 2
	Livius R. Cazan	3729	

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,830,984	12-2004	Schultz et al.	438/393
*	B	US-6,346,454	02-2002	Sung et al.	438/396
*	C	US-3,297,505	01-1967	EATON JAMES J	156/89.17
*	D	US-6,730,573	05-2004	Ng et al.	438/381
*	E	US-6,329,234	12-2001	Ma et al.	438/210
*	F	US-6,670,237	12-2003	Loh et al.	438/253
*	G	US-6,498,092	12-2002	Lee et al.	438/634
*	H	US-6,661,079	12-2003	Bikulcius, Simon	257/532
*	I	US-6,645,810	11-2003	Ng et al.	438/253
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Lee et al., Ultrathin Hafnium Oxide with Low Leakage and Excellent Reliability for Alternative Gate Dielectric Application, 1999, IEEE□□
	V	Chang et al., Rapid thermal chemical vapor deposition of zirconium oxide for metal-oxide-semiconductor field effect transistor application, 2001. American Vacuum Society
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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